

Summary

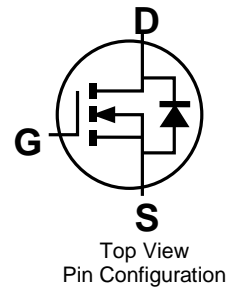
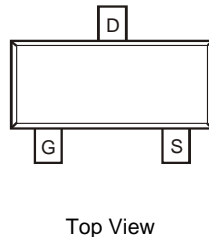
$V_{(BR)DSS}$	$R_{DS(ON)}$ max	I_D max $T_A = +25^\circ\text{C}$
60V	85 m Ω @ $V_{GS} = 10\text{V}$	2.5A
	120 m Ω @ $V_{GS} = 4.5\text{V}$	2.0A

Description

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- DC-DC Converters
- Power Management Functions
- Backlighting



Features and Benefits

- N MOSFET
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

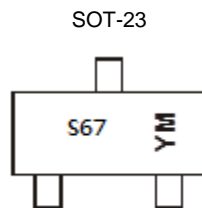
- Case: SOT-23
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Weight: 0.008 grams (Approximate)

Ordering Information (Note 4)

Product	Reel size (inches)	Tape width (mm)	Quantity per reel
DMN6075S-7	7	8	3,000
DMN6075S-13	13	8	10,000

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



S67 = Product Type Marking Code
 YM = Date Code Marking
 Y or \bar{Y} = Year (ex: B = 2014)
 M = Month (ex: 9 = September)

Date Code Key

Year	2014	2015	2016	2017	2018	2019	2020
Code	B	C	D	E	F	G	H

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	60	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 5) V _{GS} = 10V	Steady State	T _A = +25°C	I _D	2.0	A
		T _A = +70°C		1.5	
Continuous Drain Current (Note 6) V _{GS} = 10V	Steady State	T _A = +25°C	I _D	2.5	A
		T _A = +70°C		2.0	
Pulsed Drain Current (10µs pulse, duty cycle = 1%)			I _{DM}	12	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	T _A = +25°C	P _D	0.8	W
	T _A = +70°C		0.5	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{θJA}	157	°C/W
Total Power Dissipation (Note 6)	T _A = +25°C	P _D	1.15	W
	T _A = +70°C		0.7	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{θJA}	110	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	60	—	—	V	V _{GS} = 0V, I _D = 250µA
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	—	—	1.0	µA	V _{DS} = 60V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±16V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(th)}	1	—	3	V	V _{DS} = V _{GS} , I _D = 250µA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	69	85	mΩ	V _{GS} = 10V, I _D = 3.2A
			75	120		V _{GS} = 4.5V, I _D = 2.8A
Diode Forward Voltage	V _{SD}	—	—	1.2	V	V _{GS} = 0V, I _S = 2.5A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	606	—	pF	V _{DS} = 20V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	—	32.6	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	24.6	—	pF	
Gate Resistance	R _g	—	1.5	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = 10V)	Q _g	—	12.3	—	nC	V _{DS} = 30V, I _D = 3A
Total Gate Charge (V _{GS} = 4.5V)	Q _g	—	5.6	—	nC	
Gate-Source Charge	Q _{gs}	—	1.7	—	nC	
Gate-Drain Charge	Q _{gd}	—	1.9	—	nC	
Turn-On Delay Time	t _{D(on)}	—	3.5	—	ns	V _{GS} = 10V, V _{DS} = 30V, R _G = 20Ω, R _L = 50Ω
Turn-On Rise Time	t _r	—	4.1	—	ns	
Turn-Off Delay Time	t _{D(off)}	—	35	—	ns	
Turn-Off Fall Time	t _f	—	11	—	ns	

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1-inch square copper plate.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

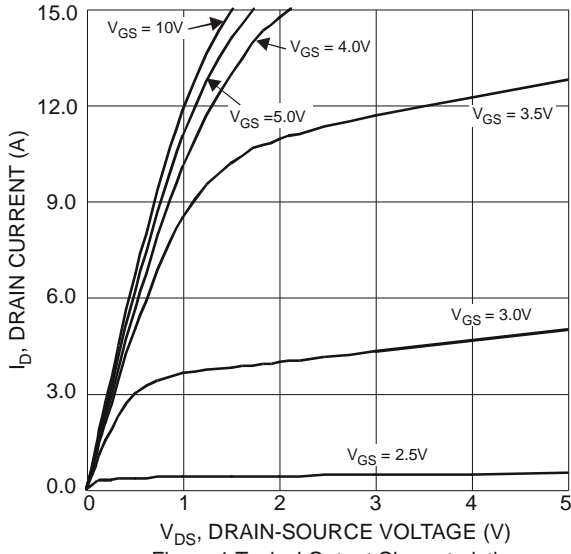


Figure 1 Typical Output Characteristics

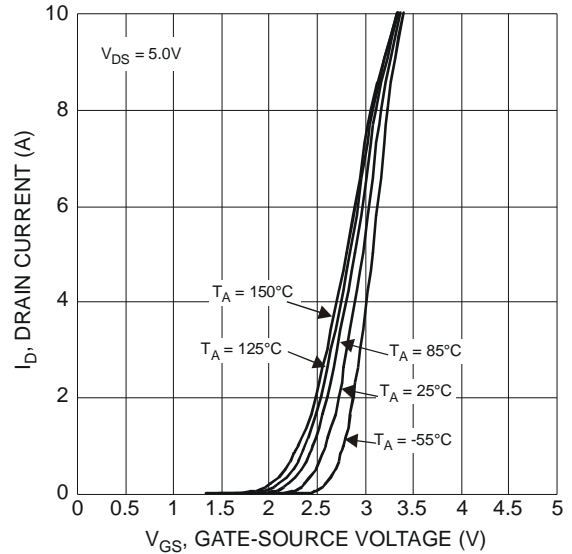


Figure 2 Typical Transfer Characteristics

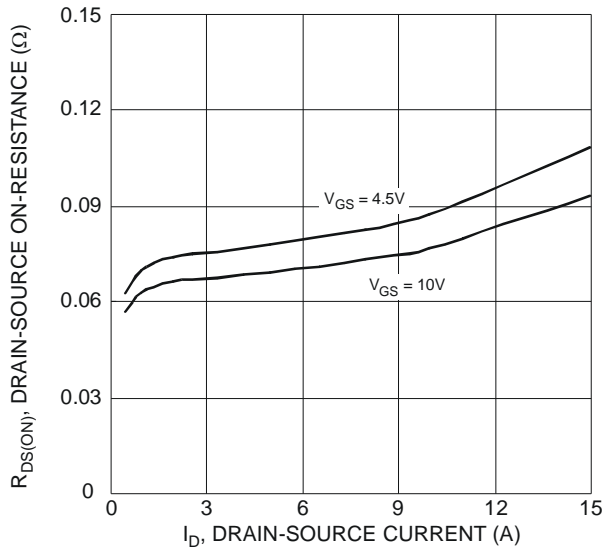


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

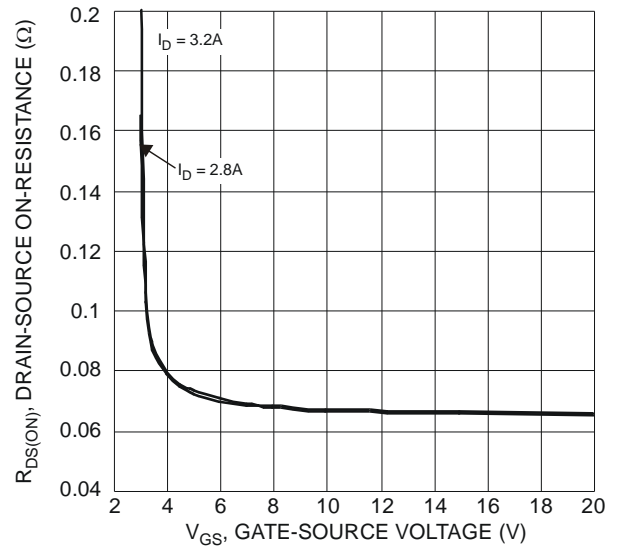


Figure 4 Typical Transfer Characteristics

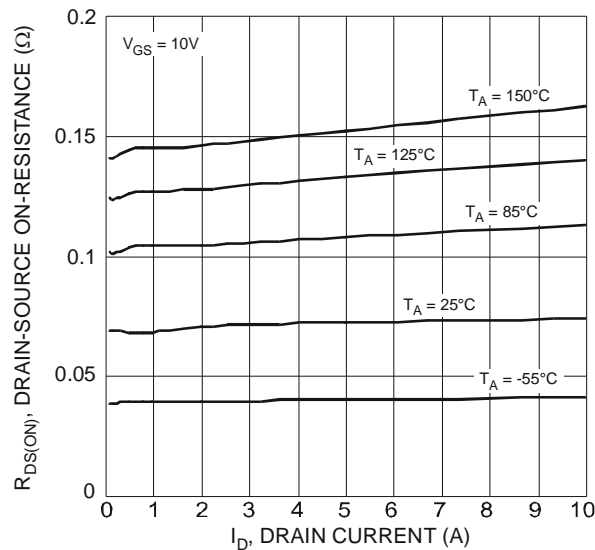


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

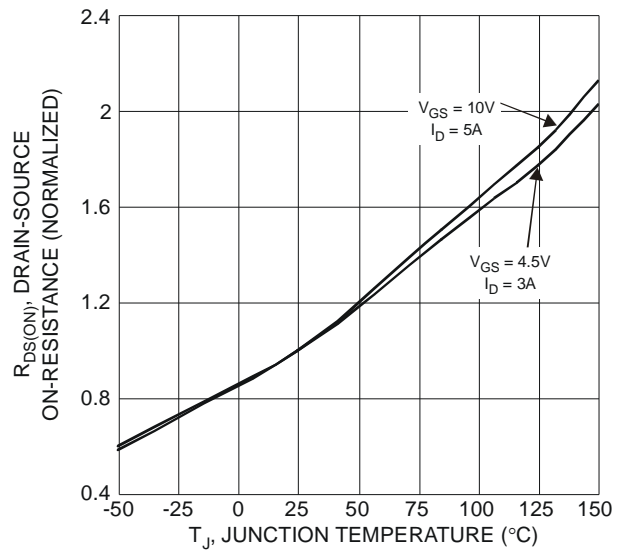


Figure 6 On-Resistance Variation with Temperature

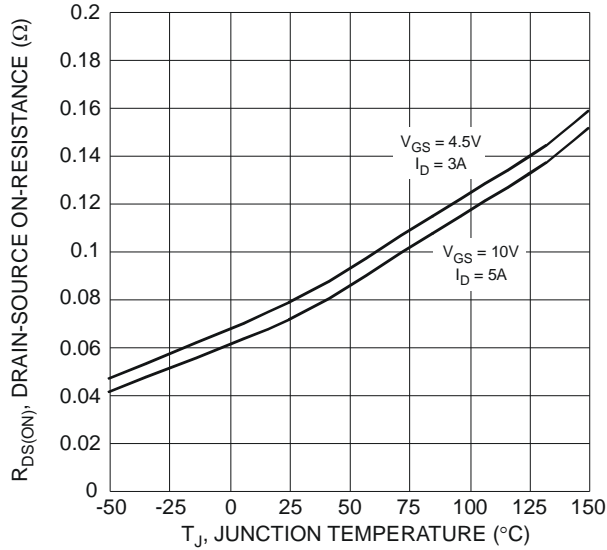


Figure 7 On-Resistance Variation with Temperature

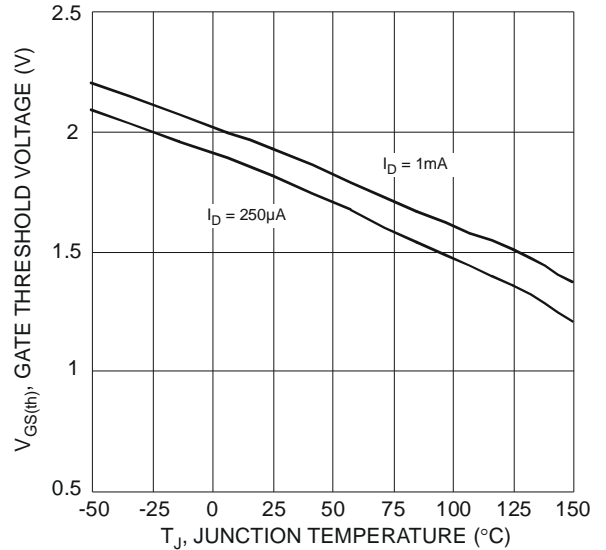


Figure 8 Gate Threshold Variation vs. Ambient Temperature

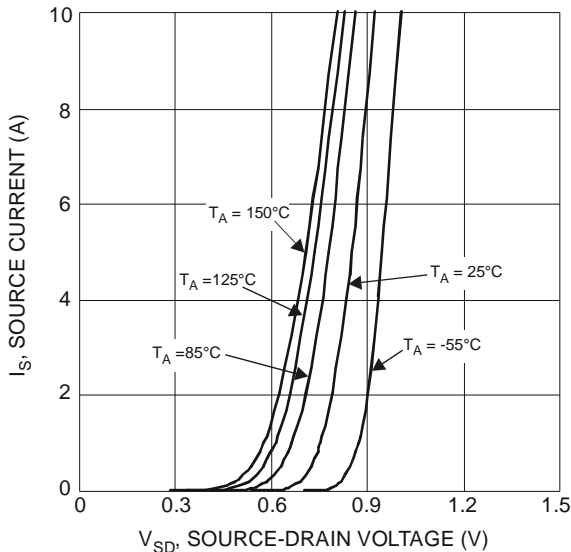


Figure 9 Diode Forward Voltage vs. Current

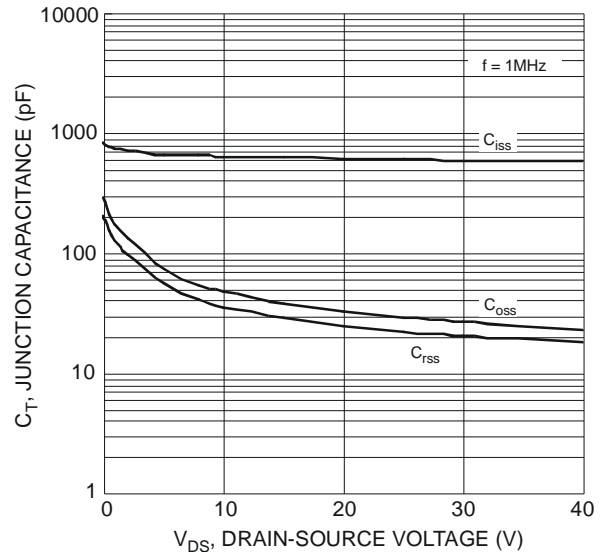


Figure 10 Typical Junction Capacitance

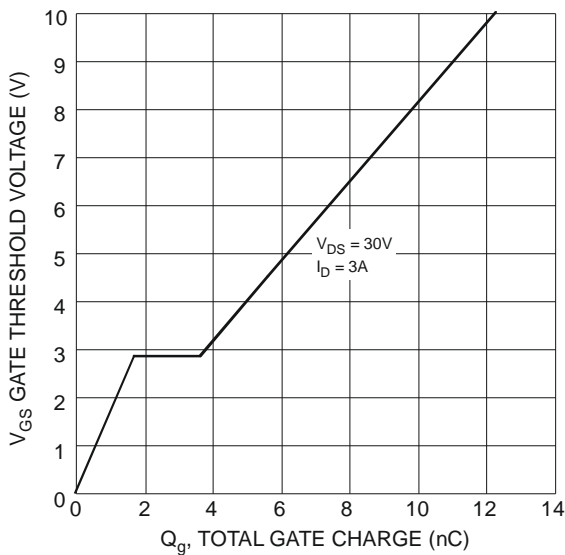


Figure 11 Gate Charge

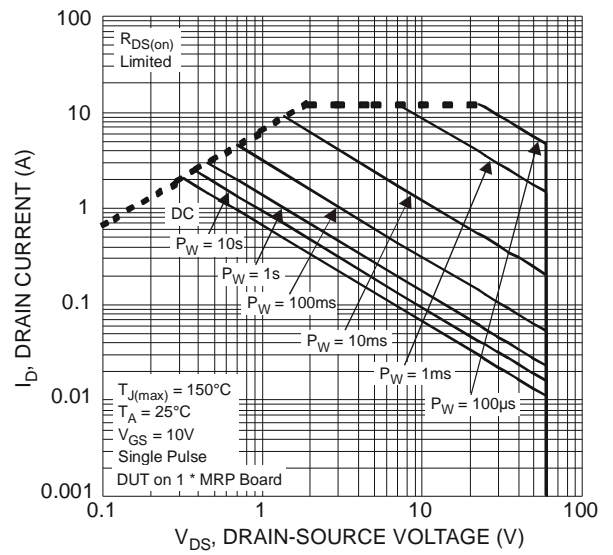


Figure 12 SOA, Safe Operation Area

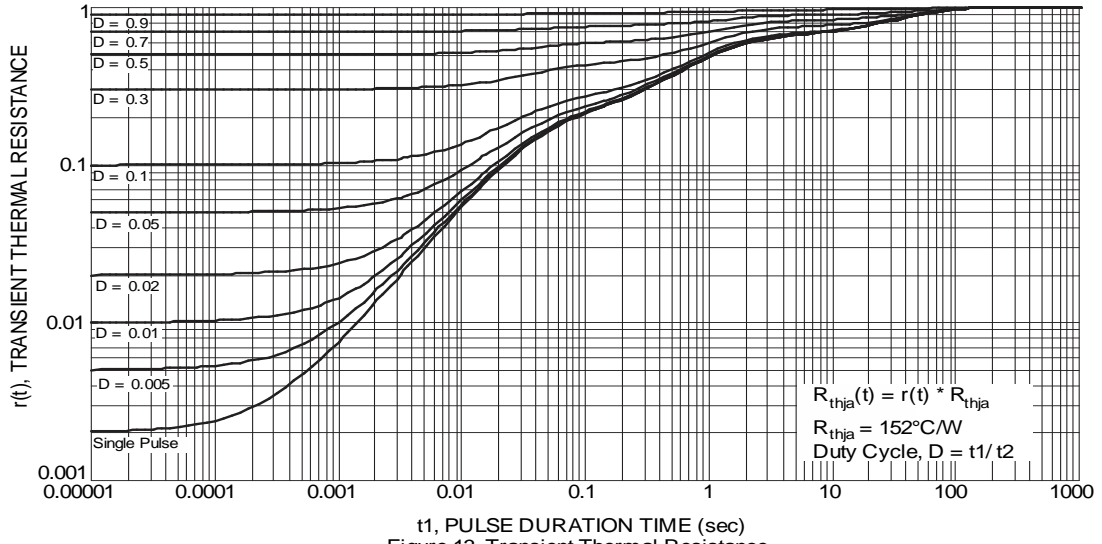
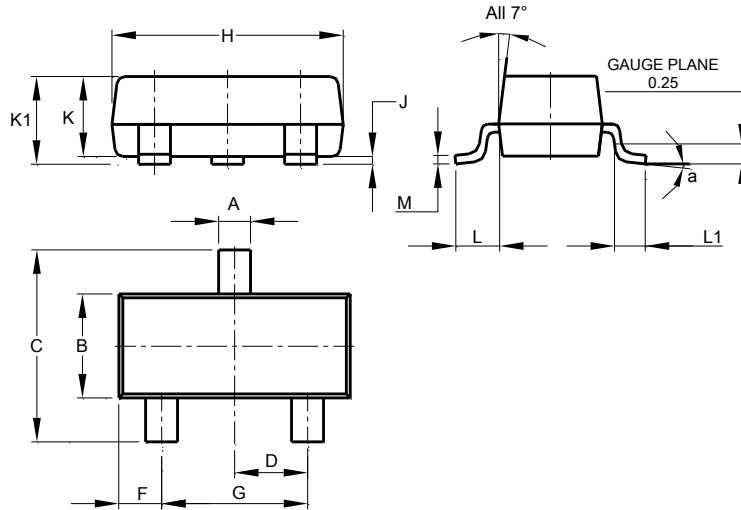


Figure 13 Transient Thermal Resistance

Package Outline Dimensions

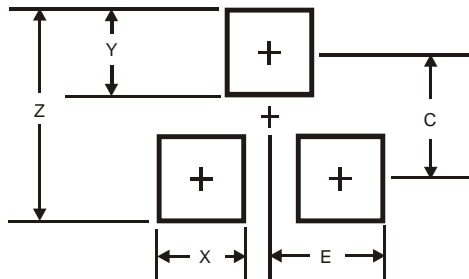
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	8°		
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35

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